NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE15H15T uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in Automotive applications and a wide variety of other applications.

General Features

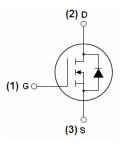
- V_{DSS} =150V, I_D =150A $R_{DS(ON)} < 8mΩ @ V_{GS}$ =10V (Typ: 6.6 mΩ)
- Good stability and uniformity with high E_{AS}
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-247 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE15H15T	NCE15H15T	TO-247	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DSS}	150	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	150	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	106	Α
Pulsed Drain Current	I _{DM}	600	Α
Maximum Power Dissipation	P _D	460	W
Derating factor		3.07	W /℃
Single pulse avalanche energy (Note 3)	E _{AS}	3100	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	18.5	V/ns



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NCE15H15T

Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}$
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Thermal Characteristic

Electrical Characteristics (T_C=25 ℃ unless otherwise noted)

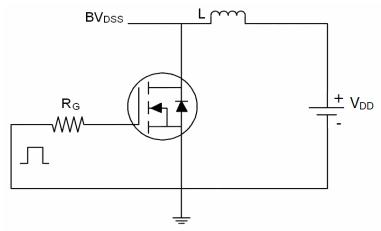
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	150	170	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±200	nA
On Characteristics			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	6.6	8	mΩ
Forward Transconductance	9 FS	V _{DS} =50V,I _D =40A	150	-	-	S
Dynamic Characteristics			•			
Input Capacitance	C _{lss}	\/ OF\/\\ 0\/	-	21000	-	PF
Output Capacitance	C _{oss}	V_{DS} =25 V , V_{GS} =0 V , F=1.0MHz	-	1446	-	PF
Reverse Transfer Capacitance	C _{rss}	Γ=1.UIVIΠZ	-	1120	-	PF
Switching Characteristics			•			
Turn-on Delay Time	t _{d(on)}		-	20	-	nS
Turn-on Rise Time	t _r	V_{DD} =30 V , I_D =2 A , R_L =15 Ω	-	110	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =2.5 Ω	-	45	-	nS
Turn-Off Fall Time	t _f		-	70	-	nS
Total Gate Charge	Qg	V _{DS} =30V,I _D =30A	-	586	-	nC
Gate-Source Charge	Q _{gs}	V _{GS} =10V	-	123	-	nC
Gate-Drain Charge	Q_{gd}		-	184	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage	V_{SD}	V _{GS} =0V,I _S =40A	-	-	1.2	V
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 75A	-	71	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note2)}$	-	106	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

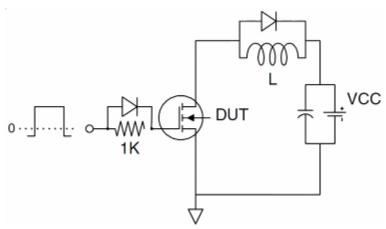
- 1. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 2. Pulse Test: Pulse Width \leq 400 μ s, Duty Cycle \leq 2%.
- 3. EAS condition: Tj=25 $^{\circ}\text{C}$,V $_{DD}$ =75V ,V $_{G}$ =10V ,L=0.5mH ,Rg=25 Ω
- 4. Isd \leqslant 125A, di/dt \leqslant 260A/ μ s, Vdd \leqslant V(BR)dss, TJ \leqslant 175°C

Test circuit

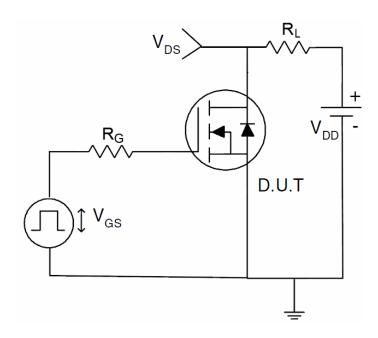
1) E_{AS} test Circuits



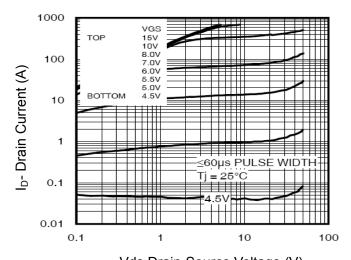
2) Gate charge test Circuit:



3) Switch Time Test Circuit:

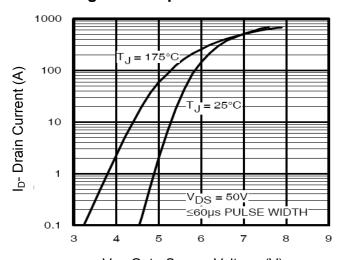


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

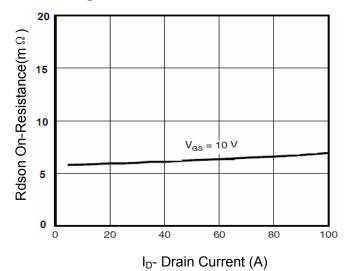
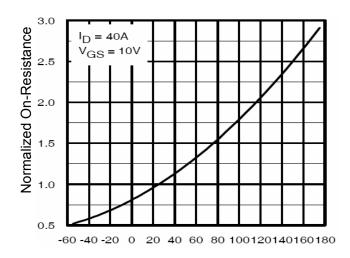


Figure 3 Rdson- Drain Current



T_J-Junction Temperature(℃)

Figure 4 Rdson-JunctionTemperature

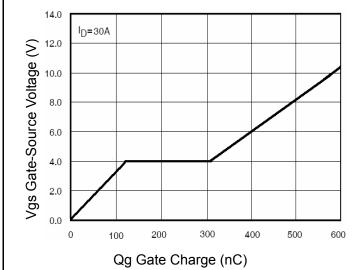


Figure 5 Gate Charge

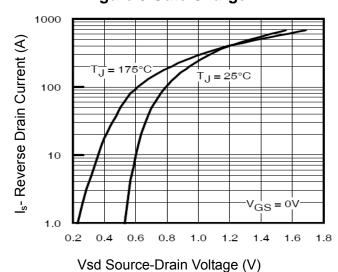
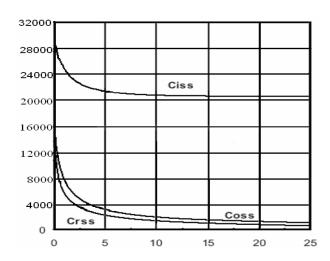
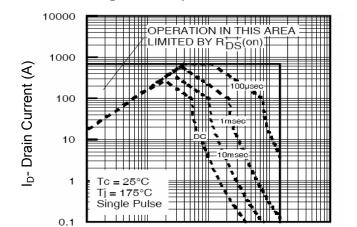


Figure 6 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds

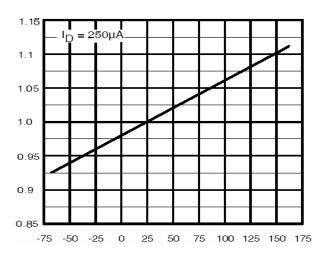


Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area

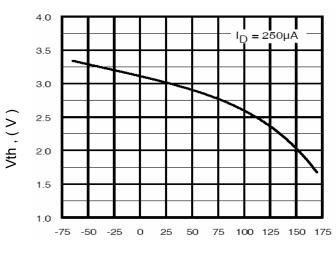
100

1000



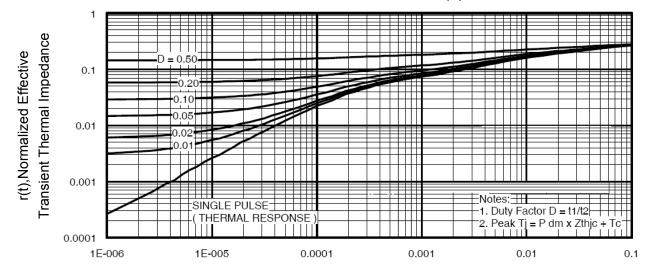
T_J-Junction Temperature(°C)

Figure 9 BV_{DSS} vs Junction Temperature



 T_J -Junction Temperature($^{\circ}$ C)

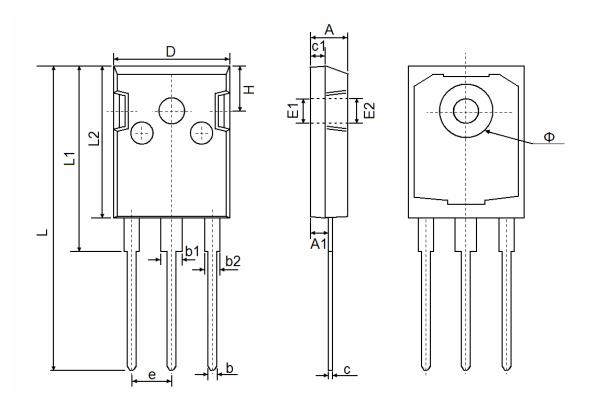
Figure 10 V_{GS(th)} vs Junction Temperatur



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

TO-247 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.850	5.150	0.191	0.200	
A1	2.200	2.600	0.087	0.102	
b	1.000	1.400	0.039	0.055	
b1	2.800	3.200	0.110	0.126	
b2	1.800	2.200	0.071	0.087	
С	0.500	0.700	0.020	0.028	
c1	1.900	2.100	0.075	0.083	
D	15.450	15.750	0.608	0.620	
E1	3.500) REF	0.138 REF		
E2	3.600	3.600 REF		? REF	
L	40.900	41.300	1.610	1.626	
L1	24.800	25.100	0.976	0.988	
L2	20.300	20.600	0.799	0.811	
Ф	7.100	7.300	0.280	0.287	
е	5.450	5.450 TYP 0.215 TYP		5 TYP	
Н	5.980) REF	0.235 REF		

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